

V

• Dumond diagrams & monochromators



- Dumond diagrams & monochromators
- Photoelectric absorption

V

- Dumond diagrams & monochromators
- Photoelectric absorption
- X-ray absorption spectroscopy

V

- Dumond diagrams & monochromators
- Photoelectric absorption
- X-ray absorption spectroscopy
- EXAFS theory

V

- Dumond diagrams & monochromators
- Photoelectric absorption
- X-ray absorption spectroscopy
- EXAFS theory

V

- Dumond diagrams & monochromators
- Photoelectric absorption
- X-ray absorption spectroscopy
- EXAFS theory

Reading Assignment: Chapter 7.4



- Dumond diagrams & monochromators
- Photoelectric absorption
- X-ray absorption spectroscopy
- EXAFS theory

Reading Assignment: Chapter 7.4

Homework Assignment #06: Chapter 6: 1,6,7,8,9 due Friday, November 15, 2024

V

- Dumond diagrams & monochromators
- Photoelectric absorption
- X-ray absorption spectroscopy
- EXAFS theory

Reading Assignment: Chapter 7.4

Homework Assignment #06: Chapter 6: 1,6,7,8,9 due Friday, November 15, 2024 Homework Assignment #07: Chapter 7: 2,3,9,10,11 due Monday, November 25, 2024

### Beam line ID32 @ ESRF





Carlo Segre (Illinois Tech)

The low temperature 3  $\times$  3 structure (dashed line) is well known but the room temperature  $\sqrt{3}\times\sqrt{3}$  surface structure (solid line) is unresolved





"Chemically resolved structure of the Sn/Ge(111) surface," T.-L. Lee, S. Warren, B.C.C. Cowie, and J. Zengenhagen, Phys. Rev. Lett. 96, 046103 (2006).

Carlo Segre (Illinois Tech)

PHYS 570 - Fall 2024

The low temperature  $3\times3$  structure (dashed line) is well known but the room temperature  $\sqrt{3}\times\sqrt{3}$  surface structure (solid line) is unresolved

A sub-monolayer of Sn is evaporated on a clean Ge(111) surface and studied using x-ray standing wave stimulated photoelectron spectroscopy



"Chemically resolved structure of the Sn/Ge(111) surface," T.-L. Lee, S. Warren, B.C.C. Cowie, and J. Zengenhagen, Phys. Rev. Lett. 96, 046103 (2006).



The low temperature  $3\times3$  structure (dashed line) is well known but the room temperature  $\sqrt{3}\times\sqrt{3}$  surface structure (solid line) is unresolved

A sub-monolayer of Sn is evaporated on a clean Ge(111) surface and studied using x-ray standing wave stimulated photoelectron spectroscopy

Below 0.2 ML, the well known 2  $\times$  2 structure is measured as a reference



"Chemically resolved structure of the Sn/Ge(111) surface," T.-L. Lee, S. Warren, B.C.C. Cowie, and J. Zengenhagen, Phys. Rev. Lett. 96, 046103 (2006).



The low temperature 3  $\times$  3 structure (dashed line) is well known but the room temperature  $\sqrt{3}\times\sqrt{3}$  surface structure (solid line) is unresolved

A sub-monolayer of Sn is evaporated on a clean Ge(111) surface and studied using x-ray standing wave stimulated photoelectron spectroscopy

Below 0.2 ML, the well known  $2\times 2$  structure is measured as a reference

Above 0.2 ML, the  $\sqrt{3}\times\sqrt{3}$  structure appears and then dominates

"Chemically resolved structure of the Sn/Ge(111) surface," T.-L. Lee, S. Warren, B.C.C. Cowie, and J. Zengenhagen, Phys. Rev. Lett. 96, 046103 (2006).









"Chemically resolved structure of the Sn/Ge(111) surface," T.-L. Lee, S. Warren, B.C.C. Cowie, and J. Zengenhagen, Phys. Rev. Lett. 96, 046103 (2006).

Carlo Segre (Illinois Tech)

PHYS 570 - Fall 2024

November 04, 2024



With an incident energy of 2.5 keV, the 2  $\times$  2 and  $\sqrt{3} \times \sqrt{3}$  structures are measured in an off-Bragg condition

"Chemically resolved structure of the Sn/Ge(111) surface," T.-L. Lee, S. Warren, B.C.C. Cowie, and J. Zengenhagen, *Phys. Rev. Lett.* **96**, 046103 (2006).

Carlo Segre (Illinois Tech)

PHYS 570 - Fall 2024

November 04, 2024 5 / 18



5/18



With an incident energy of 2.5 keV, the 2  $\times$  2 and  $\sqrt{3} \times \sqrt{3}$  structures are measured in an off-Bragg condition

The lines for both the Sn  $3d_{5/2}$  and 4d peaks in the  $2 \times 2$  phase are sharp, indicating a single chemical state

"Chemically resolved structure of the Sn/Ge(111) surface," T.-L. Lee, S. Warren, B.C.C. Cowie, and J. Zengenhagen, *Phys. Rev. Lett.* **96**, 046103 (2006).

Carlo Segre (Illinois Tech)

4d

 $3^{1/2}x3^{1/2}$ 

2x2

 $3d_{5/2}$ 

2x2

 $3^{1/2} \times 3^{1/2}$ 





With an incident energy of 2.5 keV, the 2  $\times$  2 and  $\sqrt{3} \times \sqrt{3}$  structures are measured in an off-Bragg condition

The lines for both the Sn  $3d_{5/2}$  and 4d peaks in the  $2 \times 2$  phase are sharp, indicating a single chemical state

The  $\sqrt{3} \times \sqrt{3}$  structure shows two distinct chemical shifts, with the majority component,  $l_1$ , having a slightly lower binding energy than the minority component,  $l_2$ 

"Chemically resolved structure of the Sn/Ge(111) surface," T.-L. Lee, S. Warren, B.C.C. Cowie, and J. Zengenhagen, *Phys. Rev. Lett.* **96**, 046103 (2006).

Carlo Segre (Illinois Tech)

Relative Binding Energy (eV)

By varying the energy with a resolution of 500 meV, the standing wave is swept through the Sn layer  $% \left( {{{\rm{S}}_{\rm{s}}}} \right)$ 

Sn 4d ΔE Sn 3d 1.35 e\/ 1.05 Normalized Intensity (arb. units) 0.75 0.45 0.14 -0.13 -1 -1 Relative Binding Energy (eV)

"Chemically resolved structure of the Sn/Ge(111) surface," T.-L. Lee, S. Warren, B.C.C. Cowie, and J. Zengenhagen, *Phys. Rev. Lett.* **96**, 046103 (2006).



By varying the energy with a resolution of 500 meV, the standing wave is swept through the Sn layer  $% \left( {{{\rm{S}}_{\rm{B}}} \right)$ 

As the energy is scanned around the center of the Ge(111) reflection, the fits using a mixture of Gaussian and Lorentzian line shapes show that the relative intensity,  $l_1/l_2$  varies

Sn 4d ΔE Sn 3d 1.35 ۹۱ 1.05 Normalized Intensity (arb. units) 0.75 0.45 0.14 -0.13 -1 Relative Binding Energy (eV)

"Chemically resolved structure of the Sn/Ge(111) surface," T.-L. Lee, S. Warren, B.C.C. Cowie, and J. Zengenhagen, *Phys. Rev. Lett.* 96, 046103 (2006).



By varying the energy with a resolution of 500 meV, the standing wave is swept through the Sn layer  $% \left( {{{\rm{S}}_{\rm{B}}} \right)$ 

As the energy is scanned around the center of the Ge(111) reflection, the fits using a mixture of Gaussian and Lorentzian line shapes show that the relative intensity,  $l_1/l_2$  varies

At  $\Delta E_{\gamma} = 0.45$  eV, the  $I_1/I_2$  ratio almost completely inverts, showing that the two atom populations are at different heights above the surface

"Chemically resolved structure of the Sn/Ge(111) surface," T.-L. Lee, S. Warren, B.C.C. Cowie, and J. Zengenhagen, *Phys. Rev. Lett.* **96**, 046103 (2006).





The normalized peak intensities can be fitted to extract the relative positions of the two populations of atoms and their atomic ratio

"Chemically resolved structure of the Sn/Ge(111) surface," T.-L. Lee, S. Warren, B.C.C. Cowie, and J. Zengenhagen, *Phys. Rev. Lett.* **96**, 046103 (2006).







Population 1 is two times larger than population 2 and is located a height  $\Delta h = 0.23$  Å further from the Ge(111) surface

"Chemically resolved structure of the Sn/Ge(111) surface," T.-L. Lee, S. Warren, B.C.C. Cowie, and J. Zengenhagen, *Phys. Rev. Lett.* **96**, 046103 (2006).

#### Sn 4d 1+22 Normalized yield 3 Sn 3d 1+2 2 Reflectivity 0.0 Ge(1 -0.5 0.0 0.5 1.0 1.5 20 ∆E\_ (eV)





Carlo Segre (Illinois Tech)

The normalized peak intensities can be fitted to extract the relative positions of the two populations of atoms and their atomic ratio

Population 1 is two times larger than population 2 and is located a height  $\Delta h = 0.23$  Å further from the Ge(111) surface

Population 1 also has a lower binding energy, demonstrating that the binding energy is directly correlated to the height from the surface

"Chemically resolved structure of the Sn/Ge(111) surface," T.-L. Lee, S. Warren, B.C.C. Cowie, and J. Zengenhagen, *Phys. Rev. Lett.* 96, 046103 (2006).







When the diffracting planes are not precisely aligned with the surface of the crystal the asymmetry angle,  $\alpha$ , is the important parameter





When the diffracting planes are not precisely aligned with the surface of the crystal the asymmetry angle,  $\alpha$ , is the important parameter

 $0 < \alpha < heta_{Bragg}$ 



When the diffracting planes are not precisely aligned with the surface of the crystal the asymmetry angle,  $\alpha$ , is the important parameter

 $0 < \alpha < \theta_{Bragg}$ 





When the diffracting planes are not precisely aligned with the surface of the crystal the asymmetry angle,  $\alpha$ , is the important parameter

$$0 < \alpha < \theta_{Bragg}$$

$$b = \frac{\sin \theta_i}{\sin \theta_e}$$





When the diffracting planes are not precisely aligned with the surface of the crystal the asymmetry angle,  $\alpha$ , is the important parameter

$$0 < \alpha < \theta_{Bragg}$$

$$b = \frac{\sin \theta_i}{\sin \theta_e} = \frac{\sin(\theta + \alpha)}{\sin(\theta - \alpha)}$$





When the diffracting planes are not precisely aligned with the surface of the crystal the asymmetry angle,  $\alpha$ , is the important parameter

$$0 < \alpha < \theta_{Bragg}$$

$$b = \frac{\sin \theta_i}{\sin \theta_e} = \frac{\sin(\theta + \alpha)}{\sin(\theta - \alpha)} \longrightarrow H_e = \frac{H_i}{b}$$





When the diffracting planes are not precisely aligned with the surface of the crystal the asymmetry angle,  $\alpha$ , is the important parameter

$$0 < \alpha < \theta_{Bragg}$$

this leads to a beam compression

$$b = rac{\sin heta_i}{\sin heta_e} = rac{\sin( heta + lpha)}{\sin( heta - lpha)} \longrightarrow H_e = rac{H_i}{b}$$



When the diffracting planes are not precisely aligned with the surface of the crystal the asymmetry angle,  $\alpha$ , is the important parameter

$$0 < \alpha < \theta_{Bragg}$$

this leads to a beam compression

$$b = rac{\sin heta_i}{\sin heta_e} = rac{\sin( heta + lpha)}{\sin( heta - lpha)} \longrightarrow H_e = rac{H_i}{b}$$



$$\delta\theta_e = \sqrt{b}(\zeta_D \tan\theta)$$

When the diffracting planes are not precisely aligned with the surface of the crystal the asymmetry angle,  $\alpha$ , is the important parameter

$$0 < \alpha < \theta_{Bragg}$$

this leads to a beam compression

$$b = rac{\sin heta_i}{\sin heta_e} = rac{\sin( heta + lpha)}{\sin( heta - lpha)} \longrightarrow H_e = rac{H_i}{b}$$



$$\delta heta_e = \sqrt{b}(\zeta_D \tan \theta)$$
  
 $\delta heta_i = rac{1}{\sqrt{b}}(\zeta_D \tan \theta)$ 

When the diffracting planes are not precisely aligned with the surface of the crystal the asymmetry angle,  $\alpha$ , is the important parameter

$$0 < \alpha < \theta_{Bragg}$$

this leads to a beam compression

$$b = rac{\sin heta_i}{\sin heta_e} = rac{\sin( heta + lpha)}{\sin( heta - lpha)} \longrightarrow H_e = rac{H_i}{b}$$



$$\delta heta_e = \sqrt{b}(\zeta_D \tan \theta)$$
  
 $\delta heta_i = rac{1}{\sqrt{b}}(\zeta_D \tan \theta)$ 

When the diffracting planes are not precisely aligned with the surface of the crystal the asymmetry angle,  $\alpha$ , is the important parameter

$$0 < \alpha < \theta_{Bragg}$$

this leads to a beam compression

$$b = rac{\sin heta_i}{\sin heta_e} = rac{\sin( heta + lpha)}{\sin( heta - lpha)} \longrightarrow H_e = rac{H_i}{b}$$

according to Liouville's theorem, phase space is invariant so the divergence of the beam,  $\delta\theta$ , must also change

$$\delta heta_i H_i = rac{1}{\sqrt{b}} (\zeta_D an heta) b H_e$$



$$\delta heta_e = \sqrt{b}(\zeta_D \tan heta)$$
  
 $\delta heta_i = rac{1}{\sqrt{b}}(\zeta_D \tan heta)$ 

Carlo Segre (Illinois Tech)



When the diffracting planes are not precisely aligned with the surface of the crystal the asymmetry angle,  $\alpha$ , is the important parameter

$$0 < \alpha < \theta_{Bragg}$$

this leads to a beam compression

$$b = rac{\sin heta_i}{\sin heta_e} = rac{\sin( heta + lpha)}{\sin( heta - lpha)} \longrightarrow H_e = rac{H_i}{b}$$

according to Liouville's theorem, phase space is invariant so the divergence of the beam,  $\delta\theta$ , must also change



$$\delta heta_e = \sqrt{b}(\zeta_D \tan heta)$$
  
 $\delta heta_i = rac{1}{\sqrt{b}}(\zeta_D \tan heta)$ 

$$\delta heta_i H_i = rac{1}{\sqrt{b}} (\zeta_D \tan heta) b H_e = \sqrt{b} (\zeta_D \tan heta) H_e$$

Carlo Segre (Illinois Tech)
#### Asymmetric geometry

When the diffracting planes are not precisely aligned with the surface of the crystal the asymmetry angle,  $\alpha$ , is the important parameter

$$0 < \alpha < \theta_{Bragg}$$

this leads to a beam compression

$$b = rac{\sin heta_i}{\sin heta_e} = rac{\sin( heta + lpha)}{\sin( heta - lpha)} \longrightarrow H_e = rac{H_i}{b}$$

according to Liouville's theorem, phase space is invariant so the divergence of the beam,  $\delta\theta$ , must also change



$$\delta heta_e = \sqrt{b}(\zeta_D an heta)$$
  
 $\delta heta_i = rac{1}{\sqrt{b}}(\zeta_D an heta)$ 

$$\delta\theta_i H_i = \frac{1}{\sqrt{b}} (\zeta_D \tan \theta) b H_e = \sqrt{b} (\zeta_D \tan \theta) H_e = \delta\theta_e H_e$$

Carlo Segre (Illinois Tech)



The measured "rocking" curve from a two crystal system is a convolution of the Darwin curves of both crystals.

V

The measured "rocking" curve from a two crystal system is a convolution of the Darwin curves of both crystals. When the two crystals have a matched asymmetry, we get a triangle.



output divergence on left, input divergence on right

Carlo Segre (Illinois Tech)

V

The measured "rocking" curve from a two crystal system is a convolution of the Darwin curves of both crystals. When the two crystals have a matched asymmetry, we get a triangle.



output divergence on left, input divergence on right

Carlo Segre (Illinois Tech)

The measured "rocking" curve from a two crystal system is a convolution of the Darwin curves of both crystals. When the two crystals have a matched asymmetry, we get a triangle. When one asymmetry is much higher, then we can measure the Darwin curve of a single crystal.



output divergence on left, input divergence on right

Carlo Segre (Illinois Tech)

PHYS 570 - Fall 2024



9/18

V

Transfer function of an optical element parametrized by angle and wavelength.





Transfer function of an optical element parametrized by angle and wavelength. Here Darwin width is ignored.





Transfer function of an optical element parametrized by angle and wavelength. Here Darwin width is ignored.

for small angular deviations  $\sin\theta$  is linear with a slope of  $\cos\theta_B$ 





Transfer function of an optical element parametrized by angle and wavelength. Here Darwin width is ignored.

for small angular deviations  $\sin \theta$  is linear with a slope of  $\cos \theta_B$ 

non-zero diffracted beam only for points on the line





Transfer function of an optical element parametrized by angle and wavelength. Here Darwin width is ignored.

for small angular deviations  $\sin \theta$  is linear with a slope of  $\cos \theta_B$ 

non-zero diffracted beam only for points on the line

a horizontal line transfers input to output beam characteristics



# Dumond diagram: symmetric Bragg





If Darwin width is included, the Bragg condition is represented by a box

Carlo Segre (Illinois Tech)

# Dumond diagram: symmetric Bragg



If Darwin width is included, the Bragg condition is represented by a box

for a perfectly collimated (no angular divergence) input beam, a bandwidth of radiation is accepted by the crystal

Carlo Segre (Illinois Tech)



# Dumond diagram: symmetric Bragg



If Darwin width is included, the Bragg condition is represented by a box

for a perfectly collimated (no angular divergence) input beam, a bandwidth of radiation is accepted by the crystal

this input bandwidth is transferred to a similar output bandwidth which is also collimated

Carlo Segre (Illinois Tech)



# Dumond diagram: asymmetric Bragg



For an asymmetric crystal, the output beam is no longer collimated but acquires a divergence  $\alpha_e$ 



# Dumond diagram: asymmetric Bragg



For an asymmetric crystal, the output beam is no longer collimated but acquires a divergence  $\alpha_e$ 

a perfectly collimated input beam transfers to an output beam that has an angular divergence which depends on the asymmetry factor b

Carlo Segre (Illinois Tech)



# Dumond diagram: asymmetric Bragg



V

For an asymmetric crystal, the output beam is no longer collimated but acquires a divergence  $\alpha_e$ 

a perfectly collimated input beam transfers to an output beam that has an angular divergence which depends on the asymmetry factor b

this is in addition to a compression (in this case) of the beam height (Liouville's theorem!)

Carlo Segre (Illinois Tech)

PHYS 570 - Fall 2024

12/18











θ

















the transfer functions of the two crystals match and full bandwith and divergence is preserved, giving a triangle intensity curve



























the transfer function matches only in a small energy band that varies with angle of the second crystal, mapping out the Darwin curve of the first crystal



### Asymmetric monochromator at ELETTRA



"High-throughput asymmetric double-crystal monochromator of the SAXS beamline at ELETTRA," S. Bernstorff, H. Amentisch, and P. Laggner, J. Synchrotron Rad. 5, 1215-1221 (1998).

Carlo Segre (Illinois Tech)

### Asymmetric monochromator at ELETTRA



The SAXS beamline at ELETTRA has asymmetric cut crystals with  $2^\circ$  grazing incidence in order to spread the heat load

"High-throughput asymmetric double-crystal monochromator of the SAXS beamline at ELETTRA," S. Bernstorff, H. Amentisch, and P. Laggner, J. Synchrotron Rad. 5, 1215-1221 (1998).

Carlo Segre (Illinois Tech)

### Asymmetric monochromator at ELETTRA



The SAXS beamline at ELETTRA has asymmetric cut crystals with  $2^{\circ}$  grazing incidence in order to spread the heat load

The three crystals are set for single energies of 5.6, 8.0, and 16 keV with a vertical displacement of 1.5 m and asymmetry parameter, b, of 0.053, 0.078, and 0.17, respectively

"High-throughput asymmetric double-crystal monochromator of the SAXS beamline at ELETTRA," S. Bernstorff, H. Amentisch, and P. Laggner, J. Synchrotron Rad. 5, 1215-1221 (1998).

Carlo Segre (Illinois Tech)

#### Total cross section



The total cross-section for photon "absorption" includes elastic (or coherent) scattering, Compton (inelastic) scattering, and photoelectric absorption.



V

#### Total cross section



The total cross-section for photon "absorption" includes elastic (or coherent) scattering, Compton (inelastic) scattering, and photoelectric absorption.

Characteristic absorption jumps depend on the element

Carlo Segre (Illinois Tech)



#### Total cross section



The total cross-section for photon "absorption" includes elastic (or coherent) scattering, Compton (inelastic) scattering, and photoelectric absorption.

Characteristic absorption jumps depend on the element

These quantities vary significantly over many decades but can easily put on an equal footing.

Carlo Segre (Illinois Tech)



### Scaled absorption



$$T = \frac{I}{I_0} = e^{-\mu z}$$

Carlo Segre (Illinois Tech)

### Scaled absorption



$$T = \frac{I}{I_0} = e^{-\mu z}$$
$$\mu = \frac{\rho_m N_A}{M} \sigma_a$$

Carlo Segre (Illinois Tech)

PHYS 570 - Fall 2024

November 04, 2024

17 / 18
### Scaled absorption



$$T = \frac{I}{I_0} = e^{-\mu z}$$
$$\mu = \frac{\rho_m N_A}{M} \sigma_a$$
$$\sigma_a \sim \frac{Z^4}{E^3}$$

Carlo Segre (Illinois Tech)

PHYS 570 - Fall 2024

November 04, 2024

17 / 18

### Scaled absorption



$$T = \frac{I}{I_0} = e^{-\mu z}$$
$$\mu = \frac{\rho_m N_A}{M} \sigma_a$$
$$\sigma_a \sim \frac{Z^4}{E^3}$$

 $\sigma_a$  can be scaled for different elements by  $E^3/Z^4$  and plotted together

### Scaled absorption



$$T = \frac{I}{I_0} = e^{-\mu z}$$
$$\mu = \frac{\rho_m N_A}{M} \sigma_a$$
$$\sigma_a \sim \frac{Z^4}{F^3}$$

 $\sigma_{\rm a}$  can be scaled for different elements by  $E^3/Z^4$  and plotted together

remarkably, all values lie on a common curve above the K edge and between the L and K edges and below the L edge



The states are labeled according to the principal, orbital angular momentum, and total angular momentum quantum numbers, n, l, and j, respectively



The states are labeled according to the principal, orbital angular momentum, and total angular momentum quantum numbers, n, l, and j, respectively

The absorption edges are labeled according to the initial principal quantum number of the photoelectron:





The states are labeled according to the principal, orbital angular momentum, and total angular momentum quantum numbers, n, l, and j, respectively

The absorption edges are labeled according to the initial principal quantum number of the photoelectron:

$$n = 1 \longrightarrow K$$
$$n = 2 \longrightarrow L$$
$$n = 3 \longrightarrow M$$



The states are labeled according to the principal, orbital angular momentum, and total angular momentum quantum numbers, n, l, and j, respectively

The absorption edges are labeled according to the initial principal quantum number of the photoelectron:

$$n = 1 \longrightarrow K$$
$$n = 2 \longrightarrow L$$
$$n = 3 \longrightarrow M$$

Roman numerals increase from low to high values of I and j

Carlo Segre (Illinois Tech)



